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APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER	
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Jerome Chu Sidhartha Sen

APPLICANTS

TILE

Method and structure for modular, highly linear MOS capacitors using nitrogen implantation $% \left(1\right) =\left(1\right) \left(1\right) +\left(1\right) \left(1\right) \left(1\right) +\left(1\right) \left(1\right) \left($

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	ISSUING CLASSIFICATION														
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TERMINAL		DRAWINGS	·	CLAIMS ALLOWED		
L DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.	
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has been disclaimed.	(Assistant	Examiner)	(Date)	i		
The term of this patent shall not extend beyond the expiration date						
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The information disclosed herein may be rest Possession outside the U.S. Patent & Tradem					5, Sections 122, 181 and 368	
orm PTO-436A Rev. 6/99)	<u> </u>		FILED WITH:	_ , , ,	FICHE CD-RO	

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